

CLEAN VERSION OF AMENDED SPECIFICATION PARAGRAPHS

CONDUCTIVE CONTAINER STRUCTURES HAVING A DIELECTRIC CAP

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Please amend the paragraph beginning at page 6, line 28:

Fill layer 50 and container layer 40 are then removed to approximately the top of insulating layer 15 in Figure 4. Fill layer 50 and container layer 40 are preferably planarized by chemical mechanical polishing (CMP) or removed by blanket etch-back. At this stage, a container structure is defined by a portion of container layer 40 formed on the sidewalls of the opening, and a closed bottom defined by a portion of container layer 40 formed on the bottom of the opening. Through continued removal, fill layer 50 and container layer 40 are then recessed (70) to just below the surface of insulating layer 15 in Figure 5. Such removal may be accomplished through CMP with chemistry more selective to fill layer 50 and container layer 40 than insulating layer 15, or by an etch-back process.

Please amend the paragraph beginning at page 8, line 28:

In an alternative embodiment, processing of the container structure 100 proceeds as in the previous embodiment through that depicted in Figure 4, where container layer 40 and fill layer 50 are removed to the surface of insulating layer 15. As shown in Figure 10, container layer 40 is then recessed (80) below the surface of insulating layer 15 using a selective etch process. When container layer 40 contains polysilicon, a timed, wet poly etch process can be used to recess container layer 40. The wet poly etch may remove portions of fill layer 50, but will generally be selective to the polysilicon such that container layer 40 will be recessed below both insulating layer 15 and fill layer 50.